

SiC Rapid Thermal Processing

Rapid Thermal Processing lamp furnaces



- Ohmic contact annealing
- RTO of silicon carbide
- RTCVD of graphene
- From R&D to production
- Up to 1450°C
- Up 200 mm



High Temperature Rapid Thermal Processing



Zenith-150

- Silicon carbide wafers implant annealing
- Generation of graphene by sublimation
- Giant step-bunching
- High temperature annealing processes
- Up to 2000°C for 1 hour
- Up to 4°C/s